

90 V/1.0 Ω , Hermetically Sealed, Power MOSFET Optocoupler

Technical Data

HSSR-711X* 5962-9314001 *See matrix for available extensions

Features

- Dual Marked with Device Part Number and DSCC Standard Microcircuit Drawing
- ac/dc Signal & Power Switching
- Compact Solid-State Bidirectional Switch
- Manufactured and Tested on a MIL-PRF-38534 Certified Line
- QML-38534
- MIL-PRF-38534 Class H
- Space Level Processing Available
- Hermetically Sealed 8-Pin Dual In-Line Package
- Small Size and Weight
- Performance Guaranteed over -55℃ to +125℃
- Connection A 0.8 A, 1.0 Ω
- Connection B 1.6 A, 0.25 Ω
- 1500 Vdc Withstand Test Voltage
- High Transient Immunity
- 5 Amp Output Surge Current

Applications

- Military and Space
- High Reliability Systems
- Standard 28 Vdc and 48 Vdc Load Driver
- Standard 24 Vac Load Driver
- Aircraft Controls
- ac/dc Electromechanical and Solid State Relay Replacement
- I/O Modules
- Harsh Industrial Environments

Description

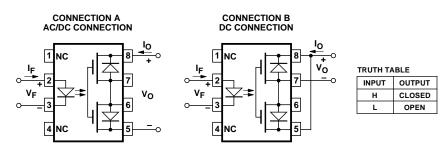
The HSSR-7110, HSSR-7111 and SMD 5962-9314001 are single channel power MOSFET optocouplers, constructed in

ceramic packages. The devices operate exactly like a solid-state relay. The products are capable of operation and storage over the full military temperature range and can be purchased as a standard product (HSSR-7110), with full MIL-PRF-38534 Class H testing (HSSR-7111), or from the DSCC Standard Microcircuit Drawing (SMD) 5962-93140.

eight-pin, hermetic, dual-in-line,

These devices may be purchased with a variety of lead bend and plating options. See Selection Guide Table for details. Standard Microcircuit (SMD) parts are available for each lead style.

Functional Diagrams



CAUTION: It is advised that normal static precautions be taken in handling and assembly of this component to prevent damage and/or degradation which may be induced by ESD.

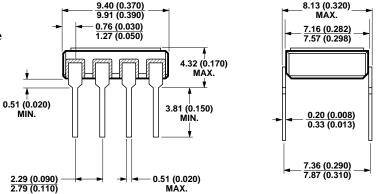
All devices are manufactured and tested on a MIL-PRF-38534 certified line and are included in the **DSCC Qualified Manufacturers** List, QML-38534 for Hybrid Microcircuits. Each device contains an AlGaAs light emitting diode optically coupled to a photovoltaic diode stack which drives two discrete power MOSFETs. The device operates as a solid-state replacement for single-pole, normally open, (1 Form A) relays used for general purpose switching of signals and loads in high reliability applications.

The devices feature logic level input control and very low output on-resistance, making them suitable for both ac and dc loads. Connection A, as shown in the Functional Diagram, allows the device to switch either ac or dc loads. Connection B, with the polarity and pin configuration as shown, allows the device to switch dc loads only. The advantage of Connection B is that the on-resistance is significantly reduced, and the output current capability increases by a factor of two.

Selection Guide–Package Styles and Lead Configuration Options

HP Part # and Options HSSR-7110 Commercial HSSR-7111 MIL-PRF-38534 Class H Gold Standard Lead Finish Solder Dipped Option #200 Butt Joint/Gold Plate Option #100 Gull Wing/Soldered Option #300 Crew Cut/Gold Plate Option #600 SMD Part # 5962-Prescript for all below Either Gold or Soldered 9314001HPX Gold Plate 9314001HPC Solder Dipped 9314001HPA Butt Joint/Gold Plate 9314001HYC Butt Joint/Soldered 9314001HYA 9314001HXA Gull Wing/Soldered Crew Cut/Gold Plate 9314001HZC Crew Cut/Soldered 9314001HZA

Outline Drawing 8-pin DIP Through Hole

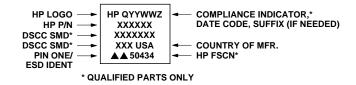


NOTE: DIMENSIONS IN MILLIMETERS (INCHES).

The devices are convenient replacements for mechanical and solid state relays where high component reliability with standard footprint lead configuration is desirable. Devices may be purchased with a variety of lead bend and plating options. See Selection Guide table for details. Standard Microcircuit Drawing (SMD) parts are available for each package and lead style.

The HSSR-7110, HSSR-7111, and SMD 5962-93140 are designed to switch loads on 28 Vdc power systems. They meet 80 V surge and \pm 600 V spike requirements.

Device Marking



Absolute Maximum Ratings

Storage Temperature Range
Operating Ambient Temperature – T_A
Junction Temperature – T_J
Operating Case Temperature – T_C
Lead Solder Temperature
(1.6 mm below seating plane)
Average Input Current – I _F
Peak Repetitive Input Current – I _{FPK}
(Pulse Width $< 100 \text{ ms}; \text{ duty cycle } < 50\%$)
Peak Surge Input Current – I _{FPK} surge 100 mA
(Pulse Width < 0.2 ms; duty cycle $< 0.1\%$)
Reverse Input Voltage – V_R
Average Output Current – Figure 2
Average Output Current – Figure 2 Connection A – I_0
Connection A – I_0
Connection A – I_0
$ \begin{array}{llllllllllllllllllllllllllllllllllll$
Connection A – I_0
$ \begin{array}{llllllllllllllllllllllllllllllllllll$
$ \begin{array}{ll} \mbox{Connection A - I}_0 & \dots & 0.8 \mbox{ A} \\ \mbox{Connection B - I}_0 & \dots & 1.6 \mbox{ A} \\ \mbox{Single Shot Output Current - Figure 3} \\ \mbox{Connection A - I}_{OPK} \mbox{ surge (Pulse width < 10 ms)} & \dots & 5.0 \mbox{ A} \\ \mbox{Connection B - I}_{OPK} \mbox{ surge (Pulse width < 10 ms)} & \dots & 10.0 \mbox{ A} \\ \end{array} $

Thermal Resistance

Maximum Output MOSFET Junction to Case – θ_{JC} = 15 °C/W

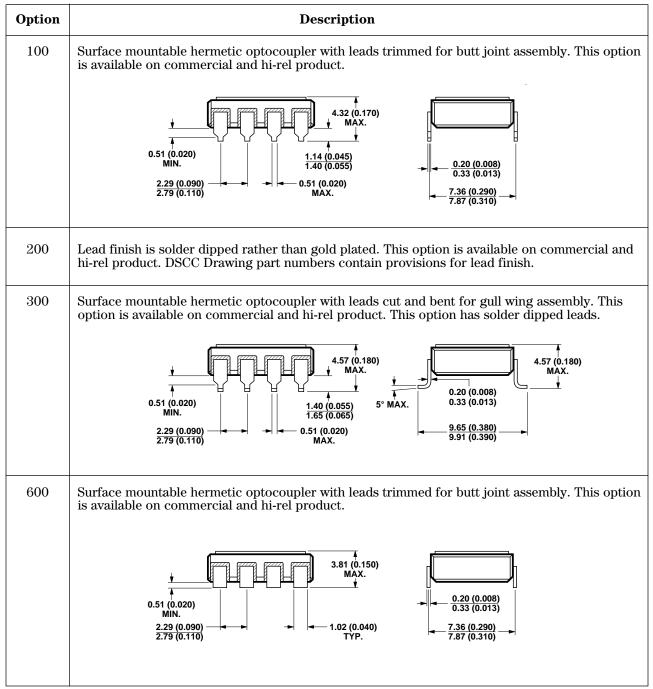
ESD Classification

(MIL-STD-883	(Method 3015)	 $(\Delta \Delta)$, Class 2

Parameter	Symbol	Min.	Max.	Units
Input Current (on)	I _{F(ON)}	5	20	mA
Input Voltage (off)	V _{F(OFF)}	0	0.6	V
Operating Temperature	T _A	-55	+125	°C

Recommended Operating Conditions

Hermetic Optocoupler Options



Note: Dimensions in millimeters (inches).

Electrical Specifications

 $T_A = -55$ °C to +125 °C, unless otherwise specified. See note 9.

Parai	neter	Sym.	Group A, Sub- group	Test Conditions	Min.	Typ.*	Max.	Units	Fig.	Notes
Output Withstand Voltage		V _{O(OFF)}	1, 2, 3	$V_{\rm F} = 0.6 \text{ V}, I_{\rm O} = 10 \ \mu \text{A}$	90	110		V	5	
Output On- Resistance	Connection A	R _(ON)	1, 2, 3	$I_F = 10 \text{ mA}, I_0 = 800 \text{ mA},$ (pulse duration $\leq 30 \text{ ms}$)		0.40	1.0	Ω	6,7	3
	Connection B			$I_{\rm F} = 10 \text{ mA}, I_{\rm O} = 1.6 \text{ A},$ (pulse duration $\leq 30 \text{ ms}$)		0.12	0.25	-		
Output Leakage Current		I _{O(OFF)}	1, 2, 3	$V_{\rm F} = 0.6 \text{ V}, V_{\rm O} = 90 \text{ V},$		10-4	10	μА	8	
Input Forward Voltage		$V_{\rm F}$	1, 2, 3	$I_F = 10 \text{ mA}$	1.0	1.24	1.7	V	9	
Input Reverse Breakdown Voltage		V _R	1, 2, 3	$I_R = 100 \ \mu A$	5.0			V		
Input-Output Insulation		I _{I-O}	1	$\begin{split} RH &\leq \ 45\%, \ t = 5 \ s, \\ V_{I-O} &= \ 1500 \ Vdc, \\ T_A &= \ 25^{\circ}C \end{split}$			1.0	μΑ		4, 5
Turn On Time		t _{on}	9, 10, 11	$I_{\rm F} = 10 \text{ mA}, V_{\rm DD} = 28 \text{ V},$ $I_{\rm O} = 800 \text{ mA}$		1.25	6.0	ms	1,10, 11,12, 13	
Turn Off Time		t _{OFF}	9,10,11	$I_{\rm F} = 10 \text{ mA},$ $V_{\rm DD} = 28 \text{ V}, I_{\rm O} = 800 \text{ mA}$		0.02	0.25	ms	1,10, 14,15	
Output Transient Rejection		$\left \frac{\mathrm{dVo}}{\mathrm{dt}} \right $	9	$\begin{split} V_{PEAK} &= 50 \text{ V}, \\ C_M &= 1000 \text{ pF}, \\ C_L &= 15 \text{ pF}, R_M \geq 1 M\Omega \end{split}$	1000			V/µs	17	
Input-Output Transient Rejection		dVio dt	9	$\begin{split} V_{DD} &= 5 \ V, \\ V_{L-O(PEAK)} &= 50 \ V, \\ R_L &= 20 \ k\Omega, \ C_L &= 15 \ pF \end{split}$	500			V/µs	18	

*All typical values are at T_{A} = 25 °C, $I_{F(ON)}$ = 10 mA, $V_{F(OFF)}$ = 0.6 V unless otherwise specified.

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Typical Characteristics

All typical values are at $T_A = 25$ °C, $I_{F(ON)} = 10$ mA, $V_{F(OFF)} = 0.6$ V unless otherwise specified.

Parameter	Symbol	Test Conditions	Тур.	Units	Fig.	Notes
Output Off-Capacitance	C _{O(OFF)}	$V_0 = 28 V, f = 1 MHz$	145	pF	16	
Output Offset Voltage	V _{os}	$I_{\rm F} = 10 \text{ mA}, I_{\rm O} = 0 \text{ mA}$	2	μV	19	7
Input Diode Temperature Coefficient	$\Delta V_F / \Delta T_A$	$I_{\rm F} = 10 \text{ mA}$	-1.4	mV/C		
Input Capacitance	C _{IN}	$V_{\rm F} = 0$ V, f = 1 MHz	20	pF		8
Input-Output Capacitance	C _{I-O}	$V_{I-O} = 0 V, f = 1 MHz$	1.5	pF		4
Input-Output Resistance	R _{I-O}	$V_{I-O} = 500 \text{ V}, t = 60 \text{ s}$	1013	Ω		4
Turn On Time With Peaking	t_{ON}	$\begin{split} I_{FPK} &= 100 \text{ mA}, \\ I_{FSS} &= 10 \text{ mA} \\ V_{DD} &= 28 \text{ V}, I_O = 800 \text{ mA} \end{split}$	0.22	ms	1	6

Notes:

1. Maximum junction to case thermal resistance for the device is $15^{\circ}C/W$, where case temperature, T_C , is measured at the center of the package bottom.

2. For rating, see Figure 4. The output power P_0 rating curve is obtained when the part is handling the maximum average output current I_0 as shown in Figure 2.

3. During the pulsed R_{ON} measurement (I_O duration <30 ms), ambient (T_A) and case temperature (T_C) are equal.

4. Device considered a two terminal device: pins 1 through 4 shorted together and pins 5 through 8 shorted together.

5. This is a momentary withstand test, not an operating condition.

6. For a faster turn-on time, the optional peaking circuit shown in Figure 1 may be implemented.

7. V_{OS} is a function of I_F , and is defined between pins 5 and 8, with pin 5 as the reference. V_{OS} must be measured in a stable ambient (free of temperature gradients).

8. Zero-bias capacitance measured between the LED anode and cathode.

9. Standard parts receive 100% testing at 25°C (Subgroups 1 and 9). SMD and class H parts receive 100% testing at 25°C, 125°C and -55°C (Subgroups 1 and 9, 2 and 10, 3 and 11 respectively).

CAUTION: Maximum Switching Frequency – Care should be taken during repetitive switching of loads so as not to exceed the maximum output current, maximum output power dissipation, maximum case temperature, and maximum junction temperature.

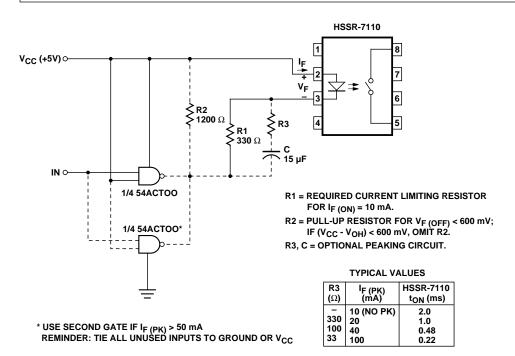


Figure 1. Recommended Input Circuit.



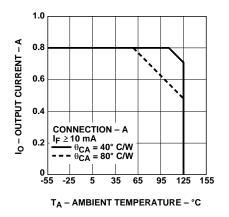


Figure 2. Maximum Average Output

Current Rating vs. Ambient

Temperature.

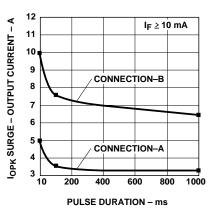


Figure 3. Single Shot (non-repetitive) Output Current vs. Pulse Duration.

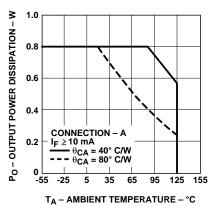


Figure 4. Output Power Rating vs. Ambient Temperature.

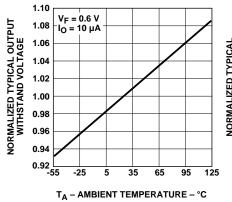


Figure 5. Normalized Typical Output Withstand Voltage vs. Temperature.

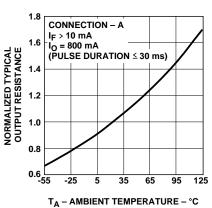


Figure 6. Normalized Typical Output Resistance vs. Temperature.

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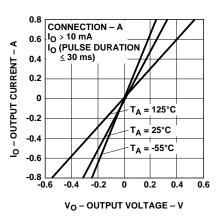
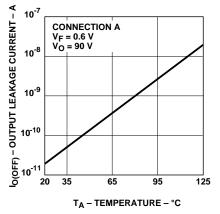


Figure 7. Typical On State Output I-V Characteristics.



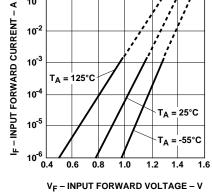


Figure 8. Typical Output Leakage Current vs. Temperature.

Figure 9. Typical Input Forward Current vs. Input Forward Voltage.

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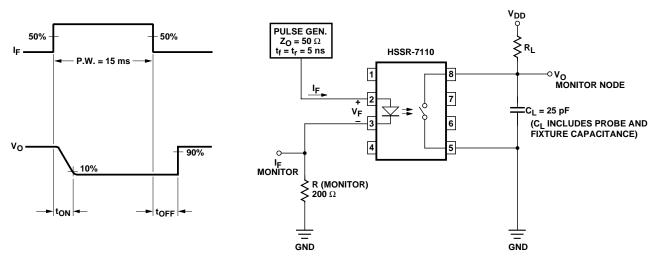
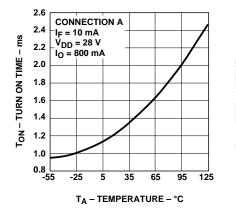
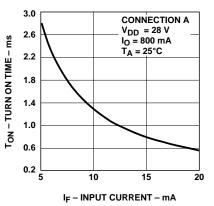


Figure 10. Switching Test Circuit for $t_{\mbox{\tiny ON}}, t_{\mbox{\tiny OFF}}.$





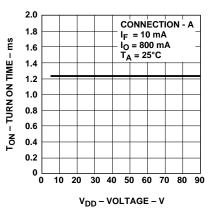


Figure 11. Typical Turn On Time vs. Temperature.

Figure 12. Typical Turn On Time vs. Input Current.

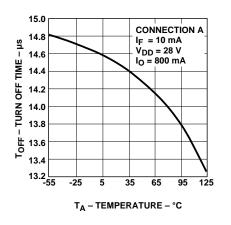


Figure 14. Typical Turn Off Time vs. Temperature.

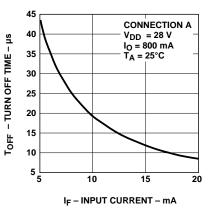


Figure 15. Typical Turn Off Time vs. Input Current.

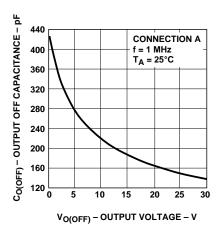


Figure 16. Typical Output Off Capacitance vs. Output Voltage.

Figure 13. Typical Turn On Time vs. Voltage.

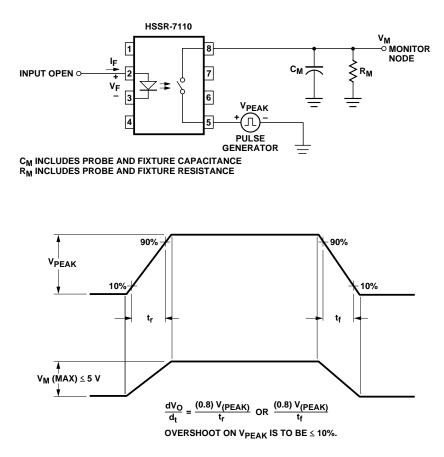


Figure 17. Output Transient Rejection Test Circuit.

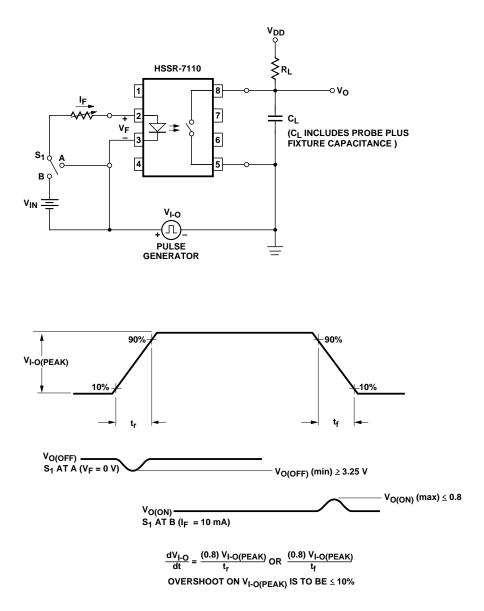


Figure 18. Input-Output Transient Rejection Test Circuit.

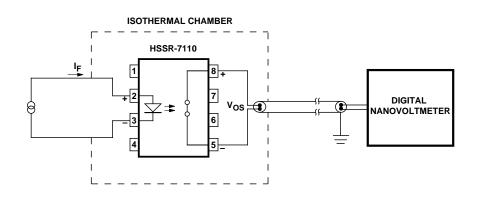
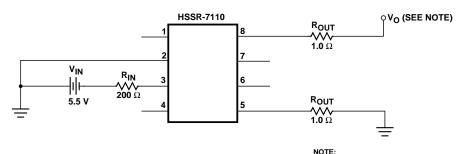


Figure 19. Voltage Offset Test Setup.

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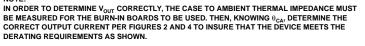
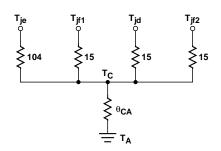


Figure 20. Burn-In Circuit.



- T_{je} = LED JUNCTION TEMPERATURE
- Tif1 = FET 1 JUNCTION TEMPERATURE
- T_{if2} = FET 2 JUNCTION TEMPERATURE
- T_{jd} = FET DRIVER JUNCTION TEMPERATURE
- T_C = CASE TEMPERATURE (MEASURED AT CENTER OF PACKAGE BOTTOM)
- T_A = AMBIENT TEMPERATURE (MEASURED 6" AWAY FROM THE PACKAGE)
- θ_{CA} = CASE-TO-AMBIENT THERMAL RESISTANCE

ALL THERMAL RESISTANCE VALUES ARE IN °C/W

Figure 21. Thermal Model.

Applications Information

Thermal Model

The steady state thermal model for the HSSR-7110 is shown in Figure 21. The thermal resistance values given in this model can be used to calculate the temperatures at each node for a given operating condition. The thermal resistances between the LED and other internal nodes are very large in comparison with the other terms and are omitted for simplicity. The components do, however, interact indirectly through θ_{CA} , the case-to-ambient thermal resistance. All heat generated flows through θ_{CA} , which raises the case temperature T_C accordingly. The value of θ_{CA} depends on the conditions of the board design and is, therefore, determined by the designer.

The maximum value for each output MOSFET junction-to-case thermal resistance is specified as 15°C/W. The thermal resistance from FET driver junction-to-case is also 15°C/W. The power dissipation in the FET driver, however, is negligible in comparison to the MOSFETs.

On-Resistance and Rating Curves

The output on-resistance, R_{ON} , specified in this data sheet, is the

resistance measured across the output contact when a pulsed current signal ($I_0 = 800 \text{ mA}$) is applied to the output pins. The use of a pulsed signal ($\leq 30 \text{ ms}$) implies that each junction temperature is equal to the ambient and case temperatures. The steadystate resistance, R_{SS} , on the other hand, is the value of the resistance measured across the output contact when a DC current signal is applied to the output pins for a duration sufficient to reach thermal equilibrium. R_{SS} includes the effects of the temperature rise of each element in the thermal model.

Rating curves are shown in Figures 2 and 4. Figure 2 specifies the maximum average output current allowable for a given ambient temperature. Figure 4 specifies the output power dissipation allowable for a given ambient temperature. Above 55°C (for $\theta_{CA} = 80$ °C/W) and 107°C (for $\theta_{CA} = 40$ °C/W), the maximum allowable output current and power dissipation are related by the expression $R_{SS} = P_0(max)/$ $(I_0(max))^2$ from which R_{ss} can be calculated. Staying within the safe area assures that the steady-state junction temperatures remain less than 150°C. As an example, for T_A = 95°C and θ_{CA} = 80°C/W, Figure 2 shows that the output current should be limited to less than

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610 mA. A check with Figure 4 shows that the output power dissipation at $T_A = 95^{\circ}C$ and $I_O = 610$ mA, will be limited to less than 0.35 W. This yields an R_{SS} of 0.94 Ω .

Design Considerations for Replacement of Electro-Mechanical Relays

The HSSR-7110 family can replace electro-mechanical relays with comparable output voltage and current ratings. The following design issues need to be considered in the replacement circuit.

Input Circuit: The drive circuit of the electro-mechanical relay coil needs to be modified so that the average forward current driving the LED of the HSSR-7110 does not exceed 20 mA. A nominal forward drive current of 10 mA is recommended. A recommended drive circuit with 5 volt VCC and CMOS logic gates is shown in Figure 1. If higher VCC voltages are used, adjust the current limiting resistor to a nominal LED forward current of 10 mA. One important consideration to note is that when the LED is turned off, no more than 0.6 volt forward bias should be applied across the LED. Even a few microamps of current may be sufficient to turn on the HSSR-7110, although it may take a considerable time. The drive circuit should maintain at least 5 mA of LED current during the ON condition. If the LED forward current is less than the 5 mA level, it will cause the HSSR-7110 to turn on with a longer delay. In addition, the power dissipation in the output power MOSFETs increases, which, in turn, may violate the power dissipation guidelines and affect the reliability of the device.

Output Circuit: Unlike electromechanical relays, the designer should pay careful attention to the output on-resistance of solid state relays. The previous section, "On-Resistance and Rating Curves" describes the issues that need to be considered. In addition, for strictly dc applications the designer has an advantage using Connection B which has twice the output current rating as Connection A. Furthermore, for dc-only applications, with Connection B the on-resistance is considerably less when compared to Connection A.

Output over-voltage protection is yet another important design consideration when replacing electro-mechanical relays with the HSSR-7110. The output power MOSFETs can be protected using Metal oxide varistors (MOVs) or TransZorbs against voltage surges that exceed the 90 volt output withstand voltage rating. Examples of sources of voltage surges are inductive load kickbacks, lightning strikes, and electro-static voltages that exceed the specifications on this data sheet. For more information on output load and protection refer to Application Note 1047.

References:

- 1. Application Note 1047, "Low On-Resistance Solid State Relays for High Reliability Applications."
- 2. Reliability Data for HSSR-7110.

MOV is a registered trademark of GE/RCA Solid State.

TransZorb is a registered trademark of General Semiconductor.

MIL-PRF-38534 Class H and DSCC SMD Test Program

Hewlett-Packard's Hi-Rel Optocouplers are in compliance with MIL-PRF-38534 Class H. Class H devices are also in compliance with DSCC drawing 5962-93140.

Testing consists of 100% screening and quality conformance inspection to MIL-PRF-38534.

www.hp.com/go/isolator

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Obsoletes 5965-1142E Printed in U.S.A. 5968-0470E (7/98)